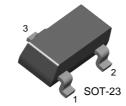




### **FMMT549 PNP Low Saturation Transistor**

### **Features**

- · This device is designed with high current gain and low saturation voltage with collector currents up to 2A continous.
- · Sourced from process PB.



1. Base 2. Emitter 3. Collector

### Absolute Maximum Ratings \* T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Unit
$V_{CEO}$	Collector-Emitter Voltage	-30	V
V <sub>CBO</sub>	Collector-Base Voltage	-35	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current - Continuous - Peak Pulse Current	-1 -2	A A
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature Range	- 55 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

### Thermal Characteristics \*

Symbol	Parameter	Value	Unit
$P_{D}$	Total Device Dissipation, by R <sub>θJA</sub> Derate above 25°C	500 4	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	250	°C/W

<sup>\*</sup> Device mounted on FR-4 PCB 4.5" X 5", mounting pad 0.02 in<sup>2</sup> of 2 oz copper.

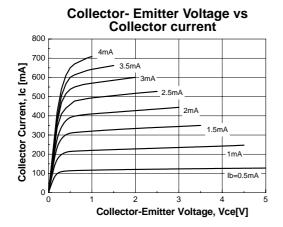
These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

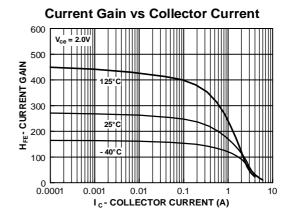
### Electrical Characteristics\* T<sub>C</sub> = 25°C unless otherwise noted

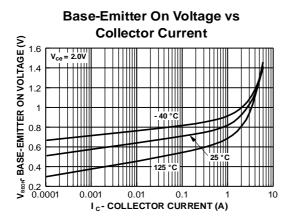
Symbol	Parameter	Conditions	Min.	Max.	Units
Off Characte	ristics			1	•
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_C = -10 \text{mA}, I_B = 0$	-30		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -100 \mu A, I_E = 0$	-35		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -100 \mu A, I_C = 0$	-5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = -30V, I_{E} = 0$ $V_{CB} = -30V, I_{E} = 0, T_{a} = 100^{\circ}C$		-100 -10	nA μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -4.0V, I <sub>C</sub> =0		-100	nA
On Characte	ristics *				
h <sub>FE</sub>	DC Current Gain	$\begin{aligned} & V_{\text{CE}} = \text{-2.0V}, \ I_{\text{C}} = \text{-50mA} \\ & V_{\text{CE}} = \text{-2.0V}, \ I_{\text{C}} = \text{-500mA} \\ & V_{\text{CE}} = \text{-2.0V}, \ I_{\text{C}} = \text{-1A} \\ & V_{\text{CE}} = \text{-2.0V}, \ I_{\text{C}} = \text{-2A} \end{aligned}$	70 100 80 40	300	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1A, I <sub>B</sub> = -100mA I <sub>C</sub> = -2A, I <sub>B</sub> = -200mA		-500 -750	mV mV
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = -1A, I_B = -100mA$		-1.25	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	I <sub>C</sub> = -1A, V <sub>CE</sub> = -2.0V		-1.0	V
Small Signal	Characterics				
f <sub>T</sub>	Current Gain Bandwidth Product	I <sub>C</sub> = -100mA, V <sub>CE</sub> = -5V, f = 100MHz	100		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = -10V, I_{E} = 0, f = 1MHz$		25	pF

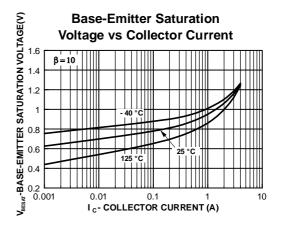
<sup>\*</sup> DC Item are tested by Pulse Test: Pulse Width≤300us, Duty Cycle≤2%

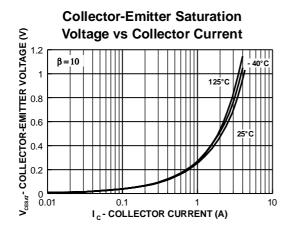
### **Typical Characteristics**

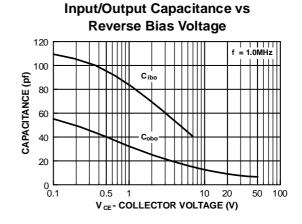






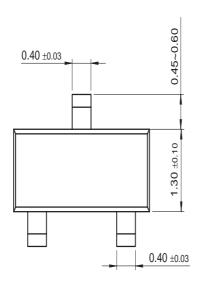


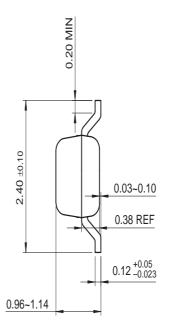


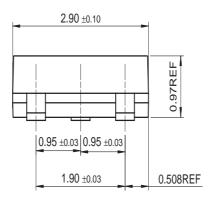


# **Package Dimensions**

# **SOT-23**







Dimensions in Millimeters

UltraFET® UniFET™ VCX™ Wire™

#### **TRADEMARKS**

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx <sup>TM</sup> ActiveArray <sup>TM</sup> Bottomless <sup>TM</sup> Build it Now <sup>TM</sup> CoolFET <sup>TM</sup> CROSSVOLT <sup>TM</sup> DOME <sup>TM</sup> EcoSPARK <sup>TM</sup> E <sup>2</sup> CMOS <sup>TM</sup> EnSigna <sup>TM</sup> FACT <sup>TM</sup> FAST <sup>®</sup> FASTr <sup>TM</sup> FPS <sup>TM</sup> FRFET <sup>TM</sup>	FACT Quiet Series <sup>TM</sup> GlobalOptoisolator <sup>TM</sup> GTO <sup>TM</sup> HiSeC <sup>TM</sup> I <sup>2</sup> C <sup>TM</sup> I-Lo <sup>TM</sup> ImpliedDisconnect <sup>TM</sup> IntelliMAX <sup>TM</sup> ISOPLANAR <sup>TM</sup> LittleFET <sup>TM</sup> MICROCOUPLER <sup>TM</sup> MicroFET <sup>TM</sup> MICROWIRE <sup>TM</sup> MSX <sup>TM</sup> MSXPro <sup>TM</sup>	OCXTM OCXProTM OCXProTM OPTOLOGIC® OPTOPLANARTM PACMANTM POPTM Power247TM PowerEdgeTM PowerSaverTM PowerTrench® QFET® QSTM QT OptoelectronicsTM Quiet SeriesTM RapidConfigureTM RapidConnectTM	SILENT SWITCHER® SMART STARTTM SPMTM StealthTM SuperFETTM SuperSOTTM-3 SuperSOTTM-6 SuperSOTTM-8 SyncFETTM TCMTM TinyBoostTM TinyBuckTM TinyPWMTM TinyPowerTM TinyPowerTM TinyLogic® TINYOPTOTM
Across the board. Around the world.™		μSerDes™	TruTranslation™
The Power Franchise®		ScalarPump™	UHC™

Programmable Active Droop™

#### **DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

#### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

### **PRODUCT STATUS DEFINITIONS**

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. I20